

RESURF LDMOS INTEGRATED STRUCTURE

Abstract of the Disclosure

A reduced surface field (RESURF) lateral diffused metal oxide semiconductor (LDMOS) integrated circuit includes a first region having a first
5 conductivity type defined in a semiconductor substrate having a second conductivity type, a body region having the second conductivity type in the first region, and a source region having the first conductivity type formed in the body region. More specifically, the body region
10 may be within a surface portion of the first region that is more heavily doped than the remainder of the of the first region.